

Additional data for 'Charge-sensing of a Ge/Si core/shell nanowire double quantum dot using a high-impedance superconducting resonator'

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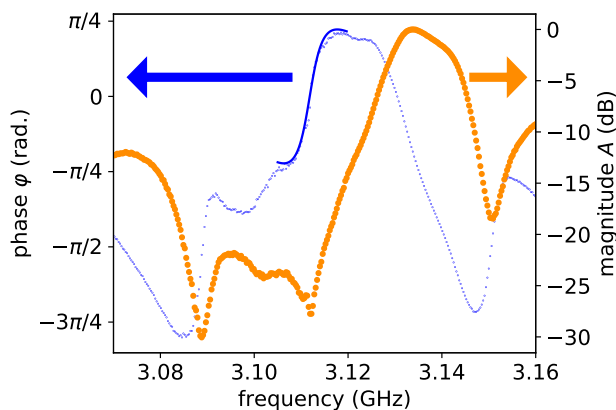


FIG. 1. Transmission through the feedline in wide frequency range

In Fig. 1 in the main text, we show the resonance curve of the resonator. When looking at a wider spectral range, which is shown in Fig. 1, it becomes apparent that the resonance is superimposed on a large standing wave background. Nonetheless, the resonator can be identified by considering a temperature-dependence scan, because its resonance frequency depends on the the large temperature-dependent kinetic inductance.

During the measurement of the data presented in Fig. 4

in the main text, several gate jumps occurred. These gate jumps result in shifts along the V_{g2} -axis. In order to focus on the relevant physics, we have omitted those shifts in Fig. 4 in the main text. Fig. 2 shows the complete data set where white annotations highlight which data was omitted in Fig. 4 (see caption of the figure).

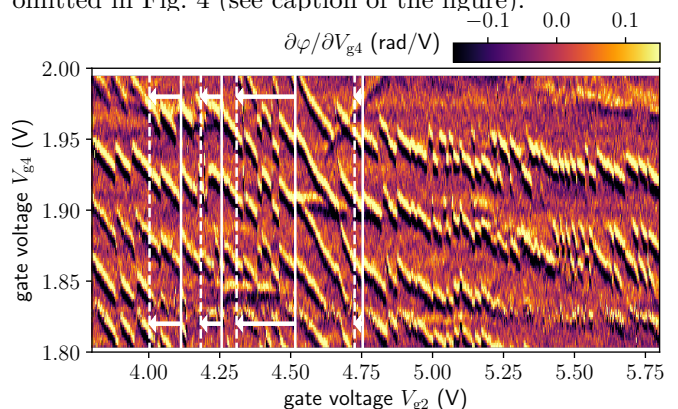


FIG. 2. Resonator response as a function of gate voltage V_{g2} and V_{g4} . This data set was used to create Fig. 4. The solid, white lines show the positions of the gate jumps. In Fig. 4, the data between the white, solid lines and the white, dashed lines, indicated by arrows, was omitted.

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